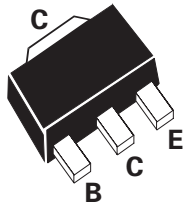
SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

Issue 4 - November 2006

FCX596

PARTMARKING DETAIL – P96



SOT89

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-220	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.3	A
Base Current	I_B	-200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-220		V	I_C=-100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200		V	I_C=-10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	I_E=-100μA
Collector Cut-Off Current	I_{CBO}		-100	nA	V_{CB}=-200V
Emitter Cut-Off Current	I_{EBO}		-100	nA	V_{EB}=-4V
Collector-Emitter Cut-Off Current	I_{CES}		-100	nA	V_{CES}=-200V
Saturation Voltages	$V_{CE(sat)}$		-0.2 -0.35	V V	I_C=-100mA,I_B=-10mA I_C=-250mA I_B=-25mA*
	$V_{BE(sat)}$		-1.0	V	I_C=-250mA,I_B=-25mA*
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.9	V	I_C=-250mA,V_{CE}=-10V*
Static Forward Current Transfer Ratio	h_{FE}	100 100 85 35	 300		I_C=-1mA, V_{CE}=-10V I_C=-100mA,V_{CE}=-10V* I_C=-250mA,V_{CE}=-10V* I_C=-400mA,V_{CE}=-10V,
Transition Frequency	f_T	150		MHz	I_C=-50mA, V_{CE}=-10V f=100MHz
Output Capacitance	C_{obo}		10	pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

For typical Characteristics graphs see FMMT596 datasheet.